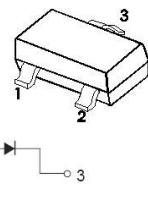


SOT-23



MARKING: 5D



SOT-23 贴片塑封二极管

**SOT-23 Plastic-Encapsulate Switching Diode****特征 Features**

开关速度小于 4.0nS; Fast Switching Device (TRR &lt; 4.0 nS)

最大功率耗散 350mW; Power Dissipation of 350mW

高稳定性和可靠性; High Stability and High Reliability

反向漏电流小; Low reverse leakage

**机械数据 Mechanical Data**

封装: SOT-23 封装 SOT-23 Small Outline Plastic Package

环氧树脂UL 易燃等级Epoxy UL: 94V-0

安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified.)

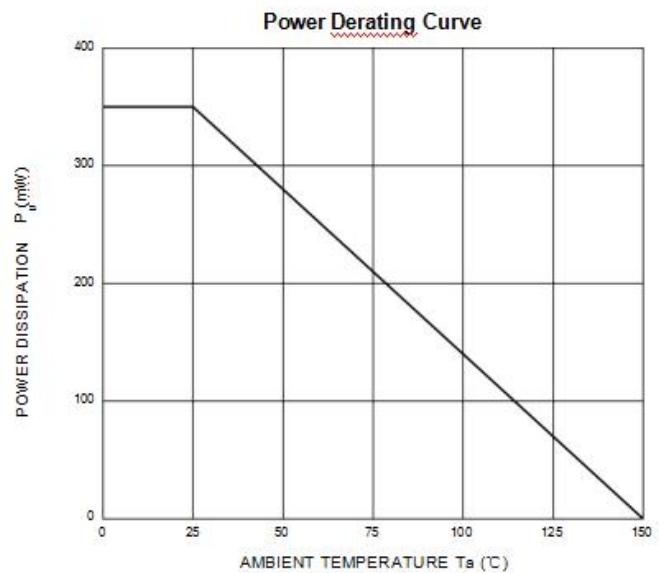
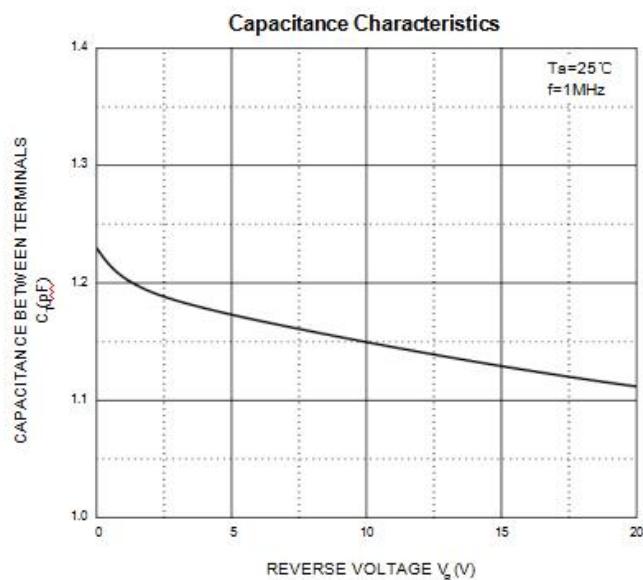
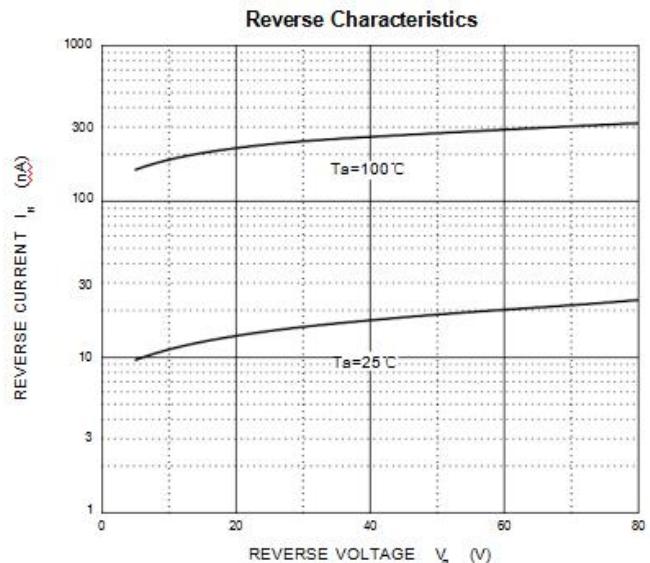
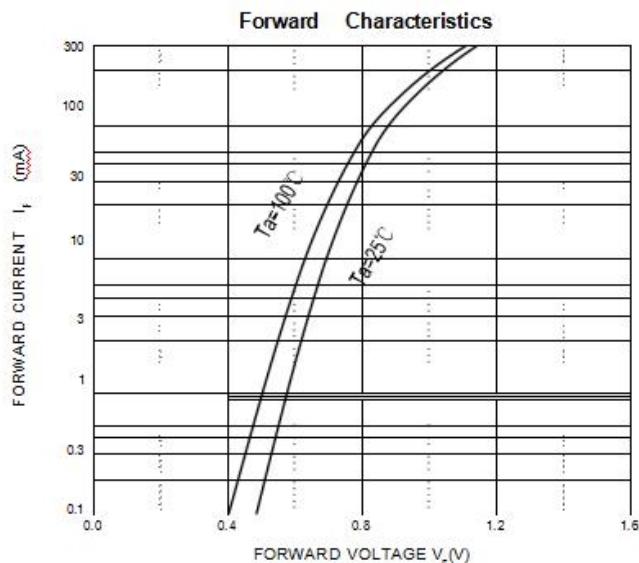
参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	VR	100	V
反向峰值电压 Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	100	V
功率消耗 Power Dissipation	P <sub>d</sub>	350	mW
平均整流电流 Average Rectified Current	I <sub>o</sub>	300	mA
正向(不重复)浪涌电流 Non-Repetitive Peak Forward Surge Current @t=8.3ms; TA=25°C	I <sub>FSM</sub>	2.0	A
工作结温 Operating junction temperature	T <sub>j</sub>	150	°C
存储温度 Storage temperature range	T <sub>s</sub>	-55~+150	°C
热阻抗 Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	357	°C/W

Valid provided that electrodes are kept at ambient temperature.

**电特性 Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

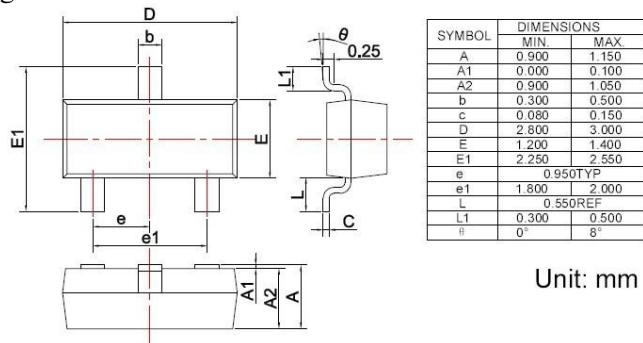
符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
V(BR)	反向电压 Reverse Voltage	IR=100uA	100		V
IR	反向漏电电流 Reverse Leakage Current	VR=75V	---	1	uA
		VR=20V	---	25	nA
VF	正向电压 Forward Voltage	IF=1mA	---	0.715	V
		IF=10mA	---	0.855	
		IF=50mA	---	1.00	
		IF=150mA	---	1.25	
TRR	反向恢复时间 Reverse Recovery Time	IF= IR=10mA	---	4	nS
		RL=100Ω			
		IRR=0.1 * IR			
CT	结电容 Capacitance	VR=0V, f=1MHZ	---	2	pF

## 典型特性曲线 Typical Characteristics



**SOT-23 PACKAGE OUTLINE**

Plastic surface mounted package

**焊盘设计参考Precautions: PCB Design**(Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs)